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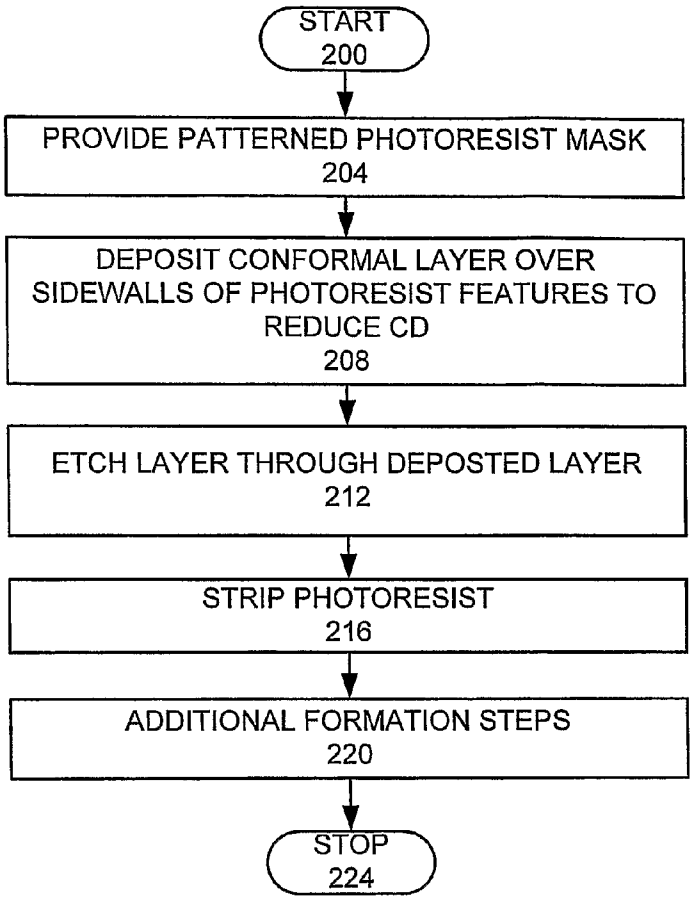
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(54) Title: REDUCTION OF FEATURE CRITICAL DIMENSIONS



(57) Abstract: A feature in a layer is provided. A photoresist layer is formed over the layer. The photoresist layer is patterned to form photoresist features with photoresist sidewalls, where the photoresist features have a first critical dimension. A conformal layer is deposited over the sidewalls of the photoresist features to reduce the critical dimensions of the photoresist features. Features are etched into the layer, wherein the layer features have a second critical dimension, which is less than the first critical dimension.

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